

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)



ON Semiconductor®

<http://onsemi.com>

Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- ESD Ratings: Machine Model, C; > 400 V
Human Body Model, 3B; > 8000 V
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V_{CEO}	40 60 80 100	Vdc
Collector-Base Voltage TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V_{CB}	40 60 80 100	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current- Continuous Peak	I_C	6.0 10	Adc
Base Current	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	65 0.52	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Unclamped Inductive Load Energy (Note 1)	E	62.5	mJ
Operating and Storage Junction, Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

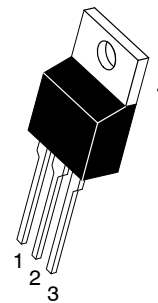
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	57	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $I_C = 2.5\text{ A}$, $L = 20\text{ mH}$, P.R.F. = 10 Hz, $V_{CC} = 10\text{ V}$, $R_{BE} = 100\ \Omega$.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

6 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 40-60-80-100 VOLTS, 65 WATTS

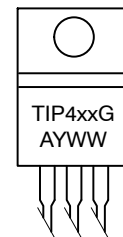


TO-220AB
CASE 221A
STYLE 1

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

TIP4xx = Device Code
xx = 1, 1A, 1B, 1C
2, 2A, 2B, 2C
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) (I _C = 30 mAdc, I _B = 0)	TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	V _{CEO(sus)}	40 60 80 100	– – – –	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0) (V _{CE} = 60 Vdc, I _B = 0)	TIP41, TIP41A, TIP42, TIP42A TIP41B, TIP41C, TIP42B, TIP42C	I _{CEO}	– –	0.7 0.7	mAdc
Collector Cutoff Current (V _{CE} = 40 Vdc, V _{EB} = 0) (V _{CE} = 60 Vdc, V _{EB} = 0) (V _{CE} = 80 Vdc, V _{EB} = 0) (V _{CE} = 100 Vdc, V _{EB} = 0)	TIP41, TIP42 TIP41A, TIP42A TIP41B, TIP42B TIP41C, TIP42C	I _{CES}	– – – –	400 400 400 400	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		I _{EBO}	–	1.0	mAdc
ON CHARACTERISTICS (Note 2)					
DC Current Gain (I _C = 0.3 Adc, V _{CE} = 4.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)		h _{FE}	30 15	– 75	–
Collector–Emitter Saturation Voltage (I _C = 6.0 Adc, I _B = 600 mAdc)		V _{CE(sat)}	–	1.5	Vdc
Base–Emitter On Voltage (I _C = 6.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	–	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 1.0 MHz)		f _T	3.0	–	MHz
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	20	–	–

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping
TIP41	TO–220	50 Units / Rail
TIP41G	TO–220 (Pb–Free)	50 Units / Rail
TIP41A	TO–220	50 Units / Rail
TIP41AG	TO–220 (Pb–Free)	50 Units / Rail
TIP41B	TO–220	50 Units / Rail
TIP41BG	TO–220 (Pb–Free)	50 Units / Rail
TIP41C	TO–220	50 Units / Rail
TIP41CG	TO–220 (Pb–Free)	50 Units / Rail
TIP42	TO–220	50 Units / Rail
TIP42G	TO–220 (Pb–Free)	50 Units / Rail
TIP42A	TO–220	50 Units / Rail
TIP42AG	TO–220 (Pb–Free)	50 Units / Rail
TIP42B	TO–220	50 Units / Rail
TIP42BG	TO–220 (Pb–Free)	50 Units / Rail
TIP42C	TO–220	50 Units / Rail
TIP42CG	TO–220 (Pb–Free)	50 Units / Rail

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)

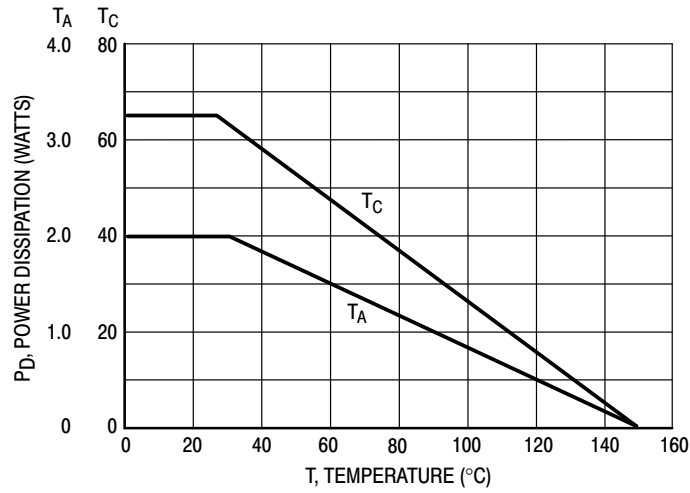


Figure 1. Power Derating

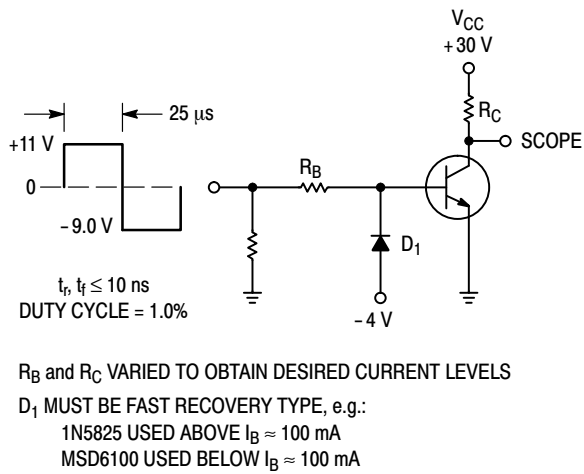


Figure 2. Switching Time Test Circuit

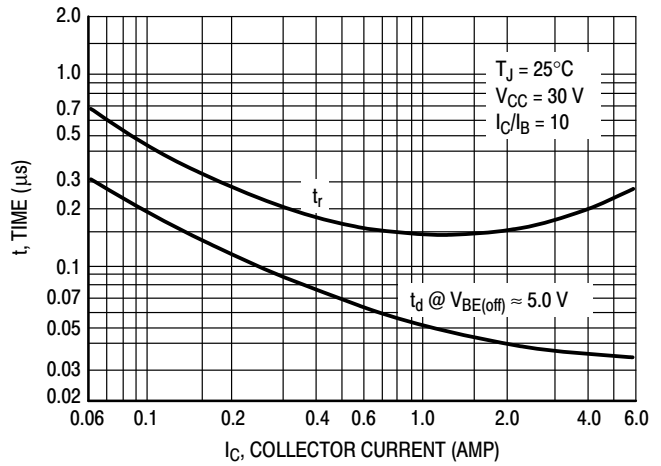


Figure 3. Turn-On Time

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)

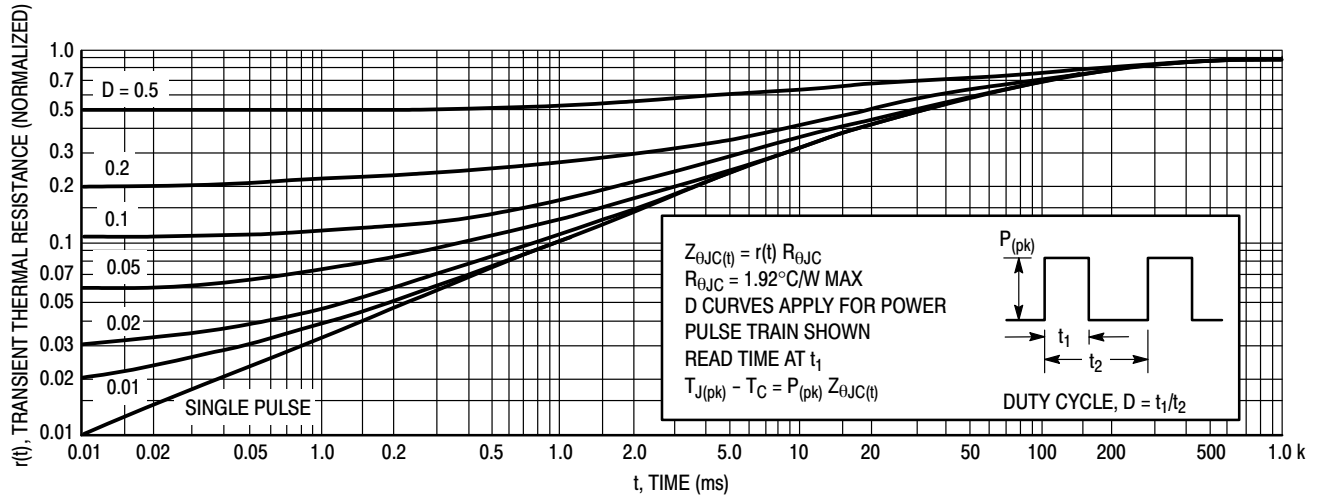


Figure 4. Thermal Response

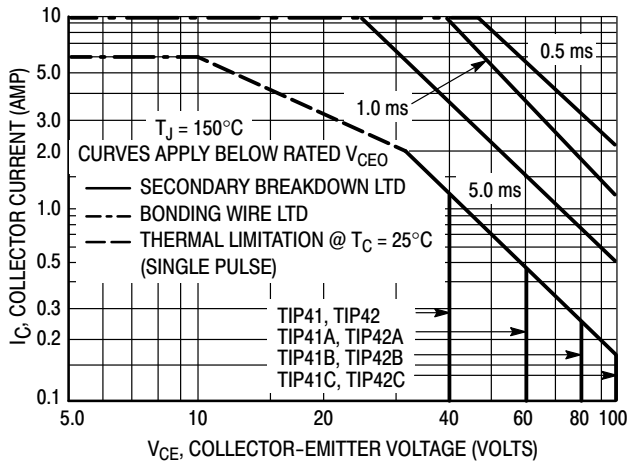


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

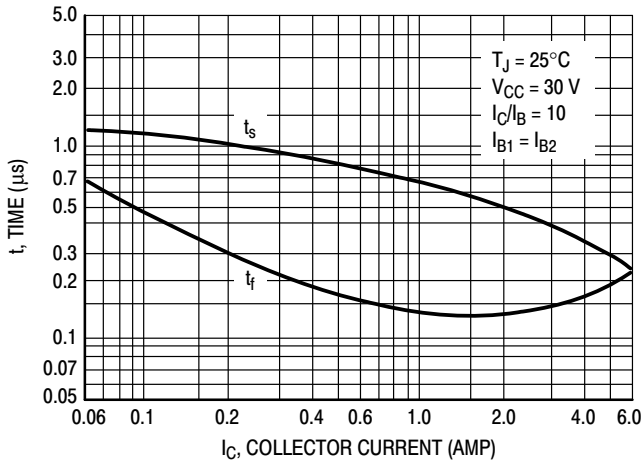


Figure 6. Turn-Off Time

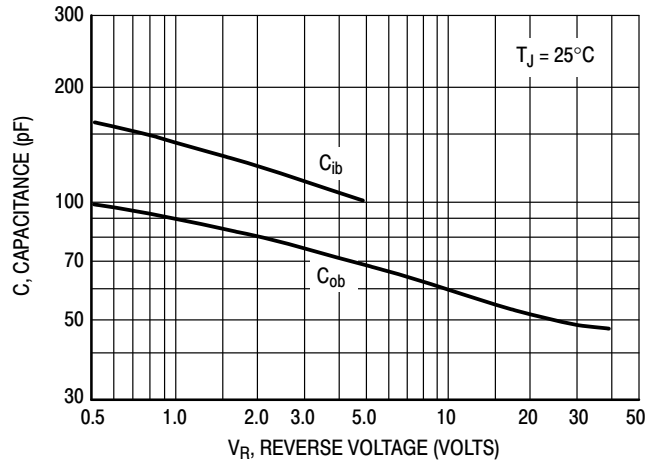


Figure 7. Capacitance

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)

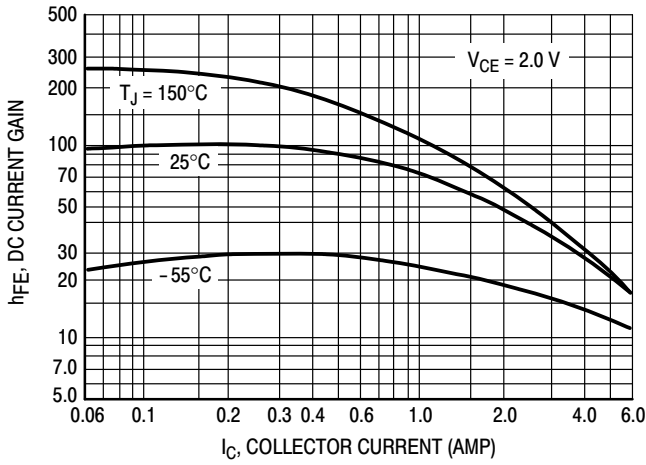


Figure 8. DC Current Gain

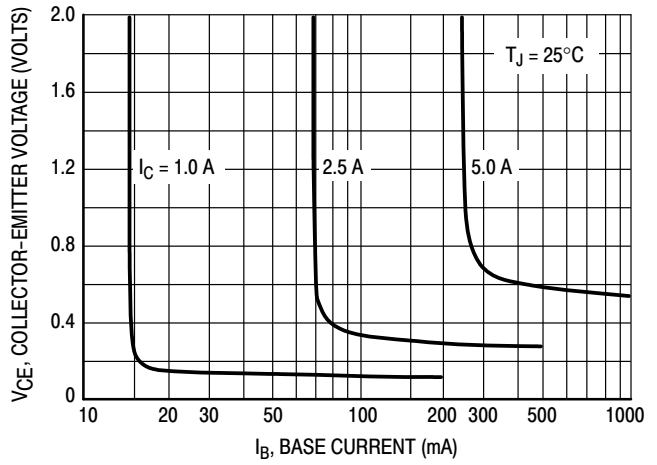


Figure 9. Collector Saturation Region

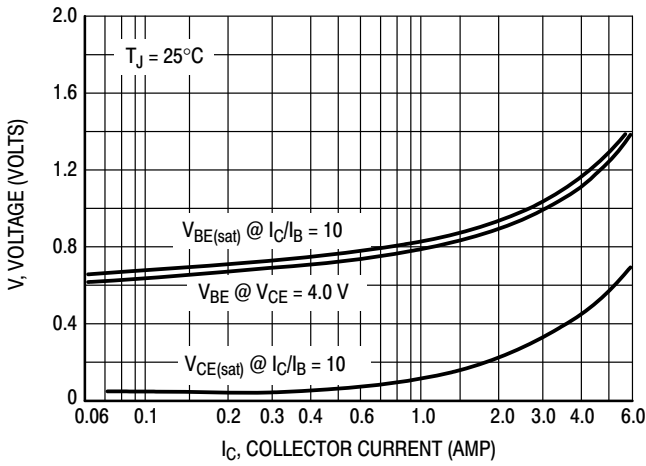


Figure 10. "On" Voltages

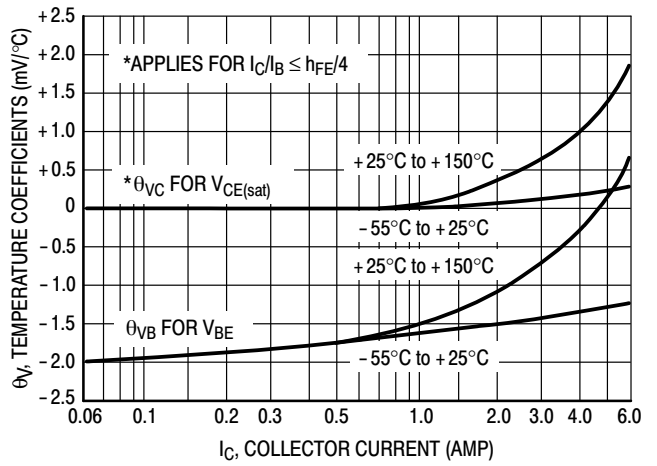


Figure 11. Temperature Coefficients

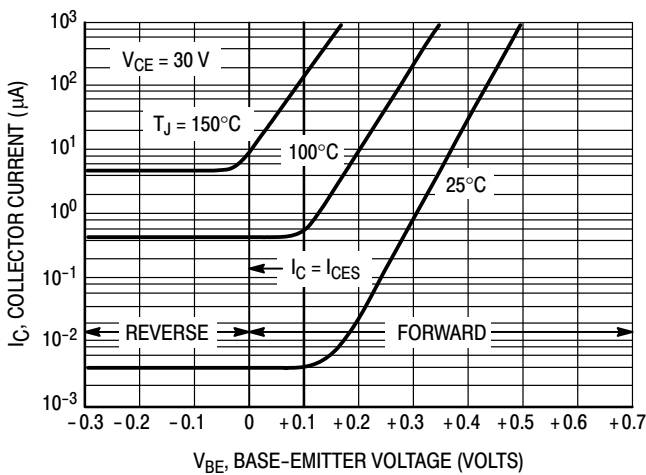


Figure 12. Collector Cut-Off Region

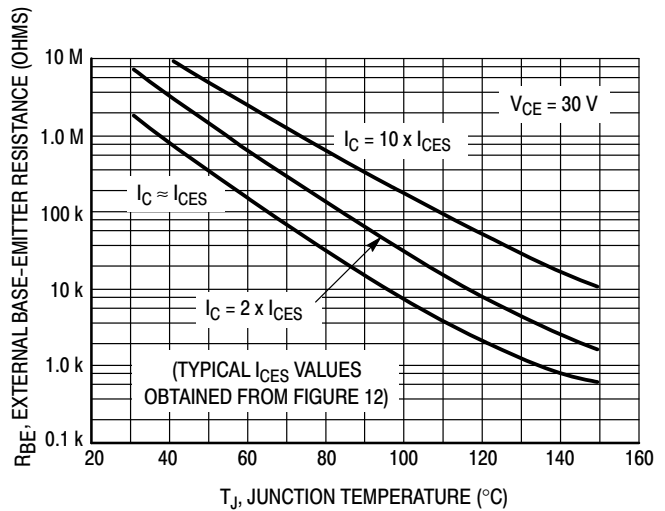
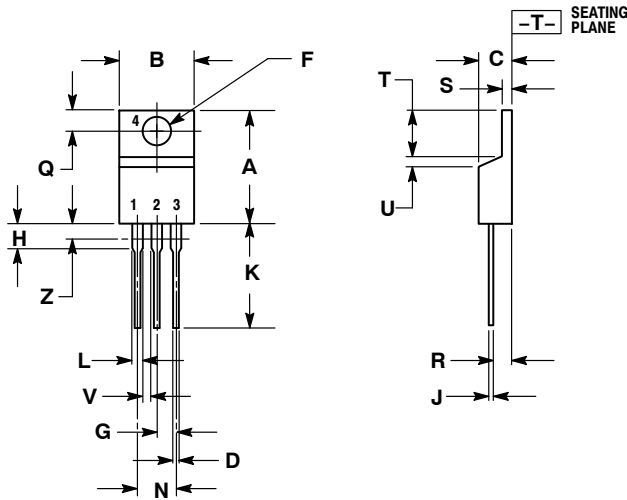


Figure 13. Effects of Base-Emitter Resistance

TIP41, TIP41A, TIP41B, TIP41C (NPN); TIP42, TIP42A, TIP42B, TIP42C (PNP)

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AG



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 1:
1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.